

ABSTRACT OF THE DISCLOSURE

An semiconductor device of the present invention, while the semiconductor device is provided with a main conductor layer, which has an end electrically connected to an electrode pad, an insulating layer, which has an opening section on the main conductor layer, and a protrudent electrode, which is electrically connected to the main conductor layer via the opening section, is further provided with a metal layer in the opening section on the main conductor layer, so that the metal layer is located between the conductor layer and the protrudent electrode. This provides a metal layer in the opening section on the main conductor layer. Thus no gap is formed between the insulating layer and the main conductor layer, even when the metal layer forms an alloy layer with a metal structuring the protrudent electrode. Thereby, water condensation in the gap is prevented. Thus, provided is a semiconductor device, which can ensure high connection reliability.

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